



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of:

Theodore W. Houston

Serial No: 10/635,185

TI-35149

Art Unit: TBD

Filed: 08/06/03

Examiner: TBD

For: Asymmetric Static Random Access Memory Device Having Reduced Bit Line Leakage

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

MAILING CERTIFICATE UNDER 37 C.F.R. §1.8(A)  
I hereby certify that the above correspondence is being deposited with the U.S. Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

*Karen Keagy* 11-14-03  
Karen Keagy Date

Dear Sir:

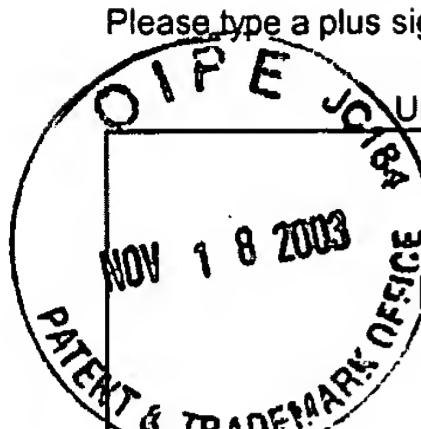
Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed PTO-1449. A copy of the noted reference is enclosed herewith.

Respectfully submitted,



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Substitute for Form 1449A/PTO <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Complete If Known	
Sheet	1	of	1	Application Number	10/635,185
				Filing Date	08/06/03
				First Named Inventor	Theodore W. Houston
				Group Art Unit	TBD
				Examiner Name	TBD
				Attorney Docket No.	TI-35149

U.S. PATENT DOCUMENTS					
Exam. Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)
		Number	Kind Code <sup>2</sup> (if known)		
AA					
AB					
AC					
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FOREIGN PATENT DOCUMENTS								
Exam. Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Name of Patentee or Applicant of Cited Doc.	Date of Pub. of Cited Doc. (mm-dd-yyyy)	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>2</sup> (if known)				
BA								
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS						
Exam. Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T <sup>2</sup>
CA		NAVID AZIZI ET AL., "Low-Leakage Asymmetric-Cell SRAM" ISLPED '02, August 12-14, 2002, Monterey, California, USA				
CB						
CC						
CD						
CE						
CF						
CG						

Examiner Signature	Date Considered
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**US and Foreign Patent Documents:** <sup>1</sup>Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

**Other Prior Art/Non-Patent Literature Documents:** <sup>1</sup>Unique citation designation number. <sup>2</sup>Applicant is to place a check mark here if English Translation is attached.